

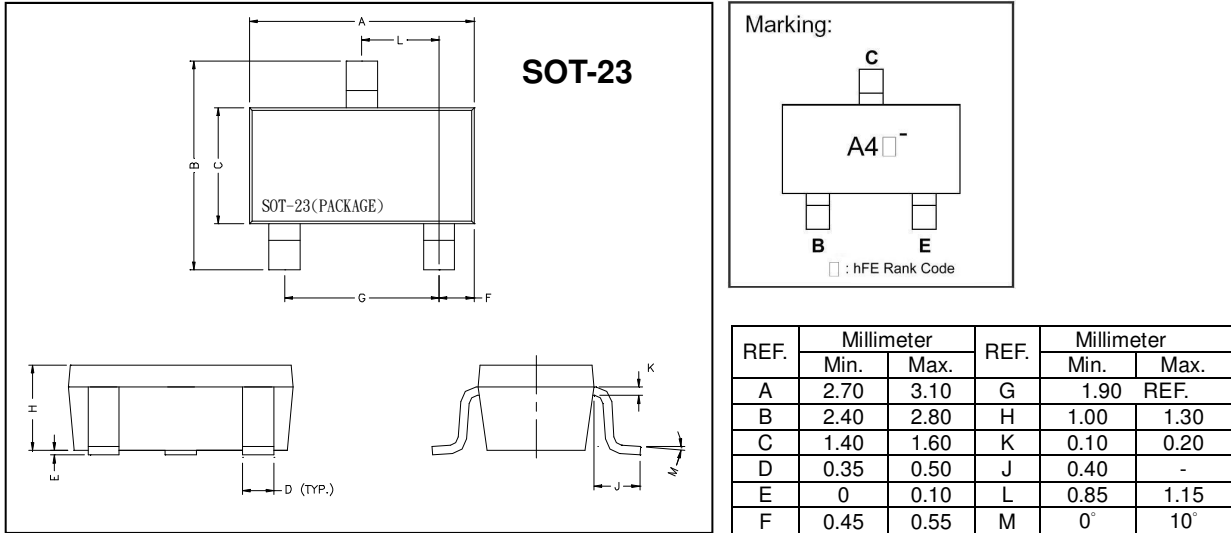
GMBT1015

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GMBT1015 is designed for use in driver stage of AF amplifier and general purpose amplification.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	-50	V
Collector to Emitter Voltage	VCEO	-50	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-150	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

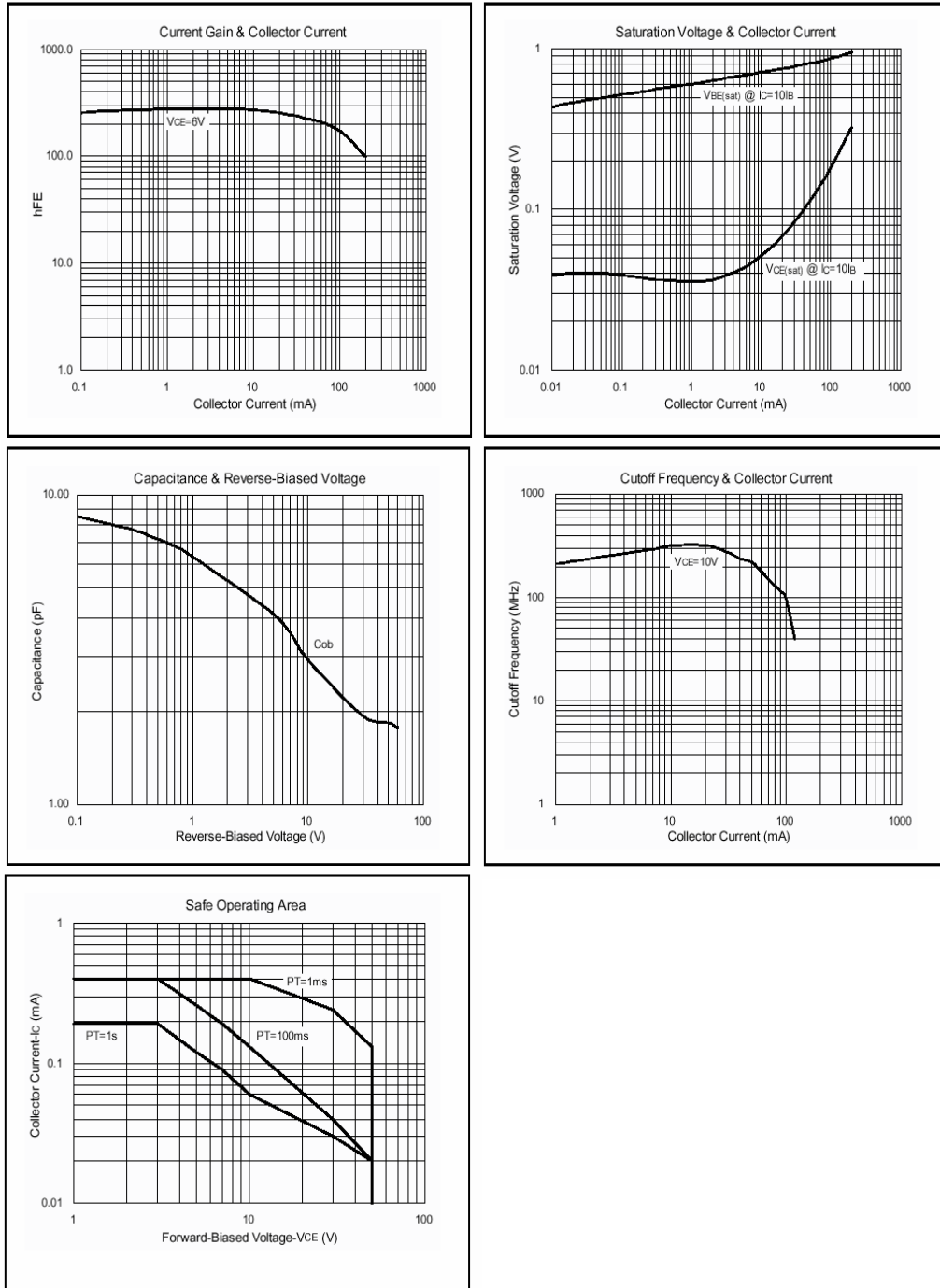
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-50	-	-	V	IC=-100uA
BVCEO	-50	-	-	V	IC=-1mA
BVEBO	-5	-	-	V	IE=-10uA
ICBO	-	-	-100	nA	VCB=-50V
IEBO	-	-	-100	nA	VEB=-5V
VCE(sat)	-	-	-300	mV	IC=-100mA, IB=-10mA
VBE(sat)	-	-	-1.1	V	IC=-100mA, IB=-10mA
hFE1	120	-	700		VCE=-6V, IC=-2mA
hFE2	25	-	-		VCE=-6V, IC=-150mA
fT	80	-	-	MHz	VCE=-10V, IC=-1mA, f=100MHz
Cob	-	-	7	pF	VCB=-10V, f=1MHz, IE=0

*Pulse Test: Pulse width ≤380us ,Duty cycle ≤ 2%

Classification Of hFE1

Rank	A4Y	A4G	A4B
Range	120-140	200-400	350-700

Characteristics Curve



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